

App. No. 10/708,618  
Amendment dated August 12, 2005  
Reply to Office action of April 18, 2005

**Amendments to the Specification (other than claims):**

Please replace paragraph [0038] with the following amended paragraph:

[0038] The Q factor and electric field pattern (radiation pattern) for a cavity made from a donor-type point defect 4 as is illustrated in Fig. 1 were simulated by the FDTD method. The simulation parameters were configured by selecting silicon for the slab 1; and setting approximately  $[[1.55 \mu\text{m}]]$  1.55  $\mu\text{m}$ , which is generally used in optical communications, for the wavelength  $\lambda$ ;  $[[0.42 \mu\text{m}]]$  0.42  $\mu\text{m}$  for the lattice constant  $a$ ;  $0.6a$  for the slab 1 thickness; and  $0.29a$  for the predetermined sectional radius of the through-holes 2.